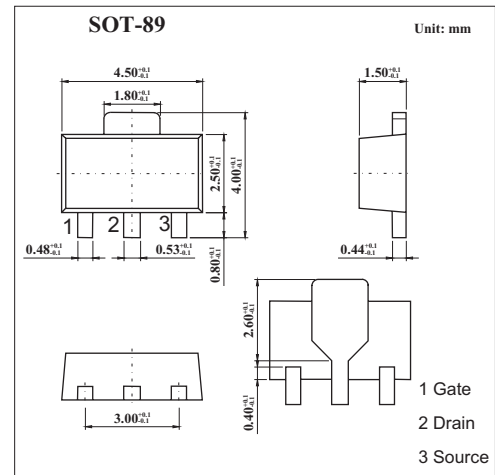


P-Channel MOS Silicon FET

2SJ287

■ Features

- Low on resistance
- Very high-speed switching
- Low-voltage drive



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage V _{GS} =0	V _{DSS}	-30	V
Gate to source voltage V _{DS} =0	V _{GSS}	±15	V
Drain current (DC)	I _D	-500	mA
Drain current(pulse) *	I _D	-2	A
Power dissipation	P _D	3.5	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μs; d ≤ 1%.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} =-30V, V _{GS} =0			-100	μA
Gate leakage current	I _{GSS}	V _{GS} =±12V, V _{DS} =0			±10	μA
Gate cut-off voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.0		-2.0	V
Forward transfer admittance	Y _{fs}	V _{DS} =-10V, I _D =-250mA	240	400		ms
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-250mA		1.5	2.2	Ω
		V _{GS} =-4V, I _D =-250mA		2.2	3.3	Ω
Input capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0, f=1MHZ		50		pF
Output capacitance	C _{oss}			35		pF
Reverse transfer capacitance	C _{rss}			10		pF
Turn-on delay time	t _{d(on)}	V _{DD} =-15V, I _D =-250mA R _L =60 Ω		7		ns
Rise time	t _r			10		ns
Turn-off delay time	t _{d(off)}			35		ns
Fall time	t _f			20		ns

■ Marking

Marking	JD
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